## SQJ170ELP

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**Vishay Siliconix** 

## Automotive N-Channel 60 V (D-S) 175 °C MOSFET



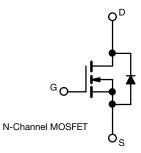
PRODUCT SUMMARY					
V <sub>DS</sub> (V)	60				
$R_{DS(on)} (\Omega)$ at $V_{GS} = 4.5 V$	0.028				
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.0163				
I <sub>D</sub> (A)	63				
Configuration	Single				
Package	PowerPAK SO-8L				

#### **FEATURES**

- TrenchFET<sup>®</sup> Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % R<sub>g</sub> and UIS tested
  Material categorization: for definitions of compliance please see

www.vishay.com/doc?99912





<b>ABSOLUTE MAXIMUM RATINGS</b>	$(T_C = 25 \ ^{\circ}C, \text{ unless})$	otherwise noted	)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V <sub>DS</sub>	60	V	
Gate-source voltage		V <sub>GS</sub>	± 20		
Continuous drain current	T <sub>C</sub> = 25 °C	I	63		
	T <sub>C</sub> = 125 °C	ID	36		
Continuous source current (diode conduction)		I <sub>S</sub>	63	А	
Pulsed drain current <sup>a</sup>		I <sub>DM</sub>	66		
Single pulse avalanche current		I <sub>AS</sub>	18.5		
Single pulse avalanche energy	L = 0.1 IIIA	E <sub>AS</sub>	17.1	mJ	
Maximum power dissipation	T <sub>C</sub> = 25 °C	D	136	W	
	T <sub>C</sub> = 125 °C	P <sub>D</sub>	45	vv	
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C	
Soldering recommendations (peak temperature) c			260	C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount <sup>b</sup>	R <sub>thJA</sub>	42	°C/W
Junction-to-case (drain)		R <sub>thJC</sub>	1.1	0/10

#### Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %

b. When mounted on 1" square PCB (FR4 material)

c. See solder profile (<u>www.vishay.com/doc?73257</u>). The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static	•	•		•			
Drain-source breakdown voltage	V <sub>DS</sub>	$V_{GS} = 0, I_D = 250 \ \mu A$		60	-	-	V
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA		2.0	2.5	v
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = 60 V	-	-	1	μA
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 125 °C	-	-	50	
	esistance <sup>a</sup> RDS(on)	$V_{GS} = 0 V$	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 175 °C	-	-	250	
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	30	-	-	А
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 10 A	-	0.0133	0.0163	
Durin country on state mariatements	P	$V_{GS} = 10 V$	I <sub>D</sub> = 10 A, T <sub>J</sub> = 125 °C	-	-	0.028	- V nA μA
Drain-source on-state resistance <sup>a</sup>	RDS(on)	$V_{GS} = 10 V$	I <sub>D</sub> = 10 A, T <sub>J</sub> = 175 °C	-	-	0.034	
		V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 10 A	-	0.0187	0.028	
Forward transconductance b	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 10 A		-	30	-	S
Dynamic <sup>b</sup>	•	•		•			
Input capacitance	C <sub>iss</sub>		V <sub>DS</sub> = 25 V, f = 1 MHz	-	832	1165	pF
Output capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$		-	411	576	
Reverse transfer capacitance				-	35	49	
Total gate charge <sup>c</sup>	Qg		V <sub>DS</sub> = 30 V, I <sub>D</sub> = 15 A	-	12	-	nC
Gate-source charge <sup>c</sup>	Q <sub>gs</sub>	$V_{GS} = 10 V$		-	4	-	
Gate-drain charge <sup>c</sup>	Q <sub>gd</sub>			-	2	-	
Gate resistance	R <sub>g</sub>	f = 1 MHz		0.6	1.3	2.0	Ω
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>	$V_{DD} = 30 \text{ V}, \text{ R}_{L} = 2.0 \Omega$ $\text{I}_{D} \cong 10 \text{ A}, \text{ V}_{\text{GEN}} = 10 \text{ V}, \text{ R}_{g} = 1 \Omega$		-	9	14	- ns
Rise time <sup>c</sup>	t <sub>r</sub>			-	3	6	
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>			-	17	26	
Fall time <sup>c</sup>	t <sub>f</sub>			-	2	4	
Source-Drain Diode Ratings and Chara	cteristics <sup>b</sup>	•		•	•		
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	123	Α
Forward voltage	V <sub>SD</sub>	I <sub>F</sub> =	I <sub>F</sub> = 10 A, V <sub>GS</sub> = 0 V		-	1.1	V
Body diode reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> = 10 A, dl/dt = 100 A/μs		-	20	40	ns
Body diode reverse recovery charge	Q <sub>rr</sub>			-	12	24	nC
Reverse recovery fall time	t <sub>a</sub>			-	11	-	
	1						ns
Reverse recovery rise time	t <sub>b</sub>			-	10	-	

Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %

b. Guaranteed by design, not subject to production testing

c. Independent of operating temperature

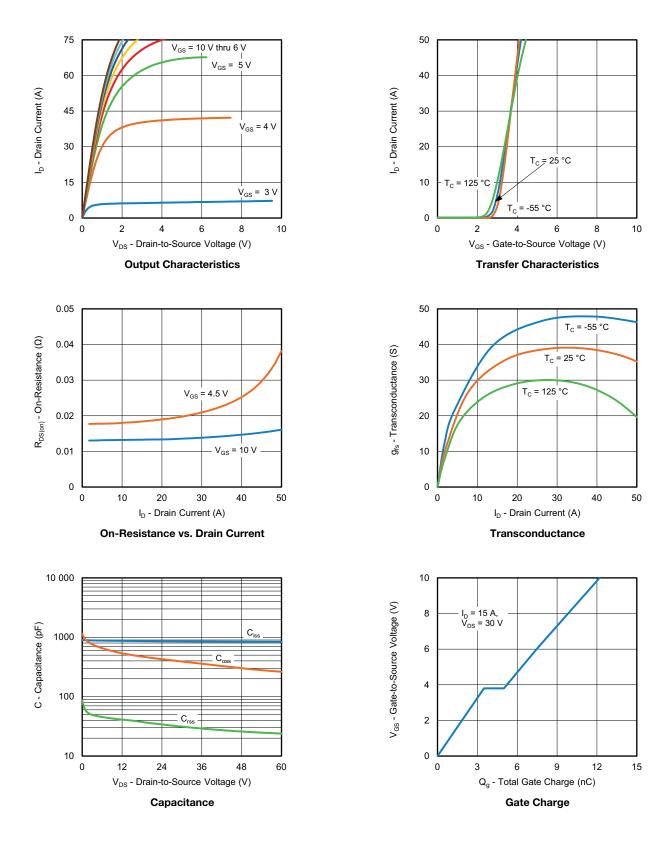
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



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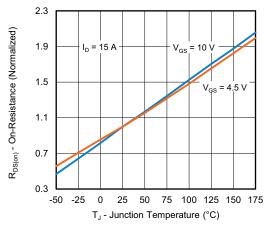
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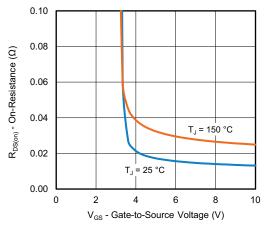
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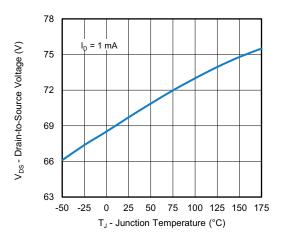
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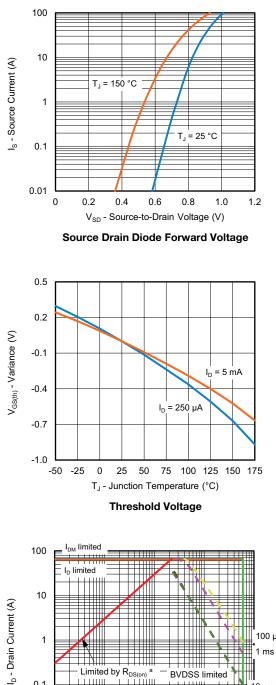
**On-Resistance vs. Junction Temperature** 

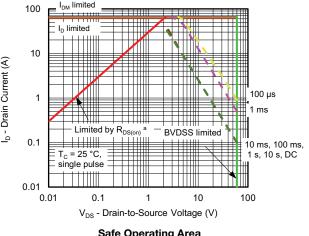


**On-Resistance vs. Gate-to Source Voltage** 

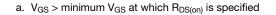


Drain Source Breakdown vs. Junction Temperature





Safe Operating Area



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Note

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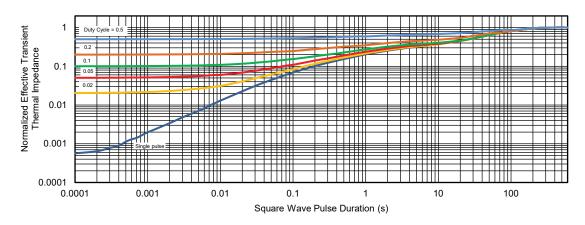
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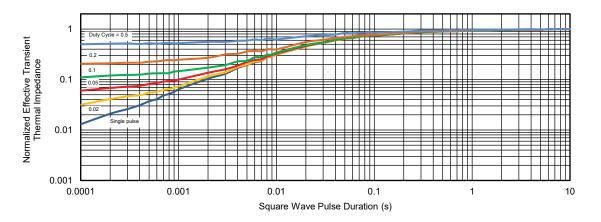
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#### TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

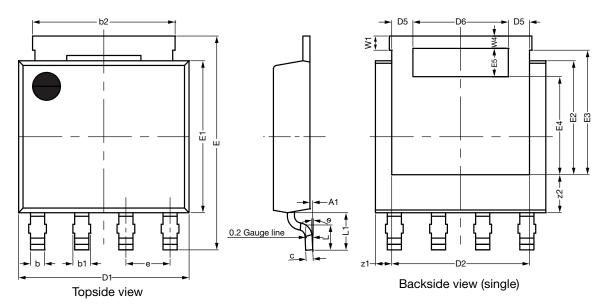
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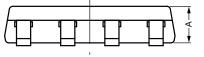
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# PowerPAK<sup>®</sup> SO-8L (PPKSO8LWLA) Case Outline 3





DIM.	MILLIMETERS			INCHES		
DIN.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
А	1.00	1.05	1.10	0.039	0.041	0.043
A1	0.00		0.127	0.000		0.005
b	0.33	0.41	0.49	0.013	0.016	0.019
b1	0.43	0.51	0.59	0.017	0.020	0.023
b2	4.00	4.10	4.20	0.157	0.161	0.165
С	0.15	0.20	0.25	0.006	0.008	0.010
D1	4.80	4.90	5.00	0.189	0.193	0.197
D2	3.86	3.96	4.06	0.152	0.156	0.160
D5	0.51	0.61	0.71	0.020	0.024	0.028
D6	2.64	2.74	2.84	0.104	0.108	0.112
е		1.27 BSC		0.050 BSC		
E	6.05	6.15	6.25	0.238	0.242	0.246
E1	4.27	4.37	4.47	0.168	0.172	0.176
E2	3.18	3.28	3.38	0.125	0.129	0.133
E3	3.48	3.58	3.68	0.137	0.141	0.145
E4	2.72	2.82	2.92	0.107	0.111	0.115
E5	0.71	0.81	0.91	0.028	0.032	0.036
L	0.62	0.72	0.82	0.024	0.028	0.032
L1	0.92	1.07	1.22	0.036	0.042	0.048
W1	0.31	0.41	0.51	0.012	0.016	0.020
W4	0.31	0.36	0.41	0.012	0.014	0.016
z1	0.37	0.47	0.57	0.015	0.019	0.022
z2	0.99	1.09	1.19	0.039	0.043	0.047
θ	0°		5°	0°		5°

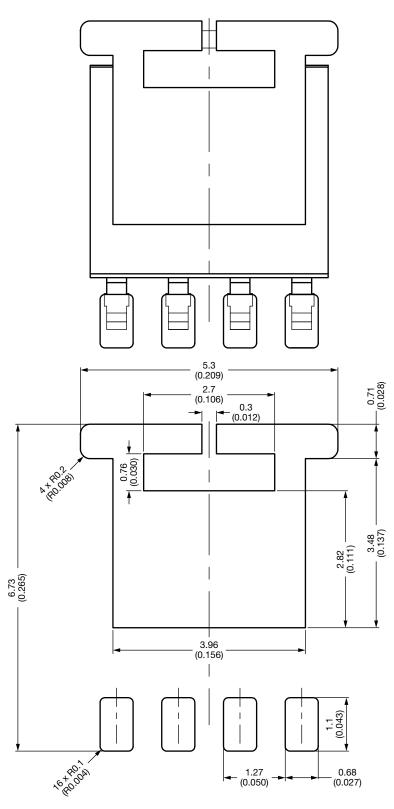
Note

• Millimeter will govern



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## **Recommended Land Pattern PowerPAK® SO-8L Single Short Ear**



Dimensions in Millimeters (Inches)

Revision: 24-Aug-2021

Document Number: 78020



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